SCHOTTKY BARRIER RECTIFIERS

Reverse Voltage: 150,200V
Forward Current: 20A

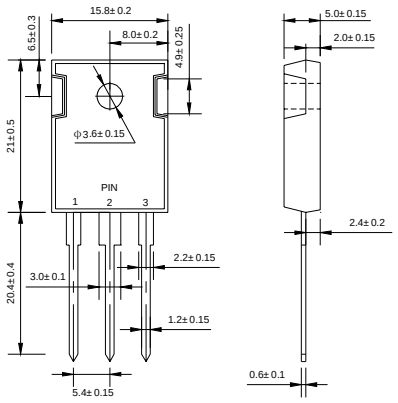
FEATURES

- Metal-Semiconductor junction with guard ring
- Epitaxial construction
- Low forward voltage drop, low swithing losses
- High surge capacity
- For use in low voltage, high frequency inverters free wheeling, and polarity protection applications
- The plastic material carries U/L recognition 94V-0

MECHANICAL DATA

- **Case:** JEDEC TO-3P, molded plastic body
- **Terminals:** Solderable per MIL-STD-750, Method 2026
- **Polarity:** As marked
- **Mounting Position:** Any
- **Weight:** 0.223 ounce, 6.3 grams

TO-3P



Dimensions in millimeters

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.
Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Parameter	Symbol	MBR20150PT	MBR20200PT	UNITS
Maximum recurrent peak reverse voltage	V_{RRM}	150	200	V
Maximum RMS voltage	V_{RWS}	135	140	V
Maximum DC blocking voltage	V_{DC}	150	200	V
Maximum average forward tolal device rectified current @T_C=120°C	$I_{(AV)}$	20		A
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load	I_{FSM}	150		A
Maximum instantaneous forward voltage @ 10A	V_F	0.95		V
Maximum reverse current @T_A=25°C at rated DC blocking voltage @T_A=100°C	I_R	0.2 50		mA
Maximum thermal resistance (Note1)	$R_{\theta JC}$	1.5		°C/W
Operating junction temperature range	T_J	-55 --- +150		°C
Storage temperature range	T_{STG}	-55 --- +150		°C

NOTES: 1. Thermal resistance from junction to case.

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FIG.1 TYPICAL FORWARD CHARACTERISTICS

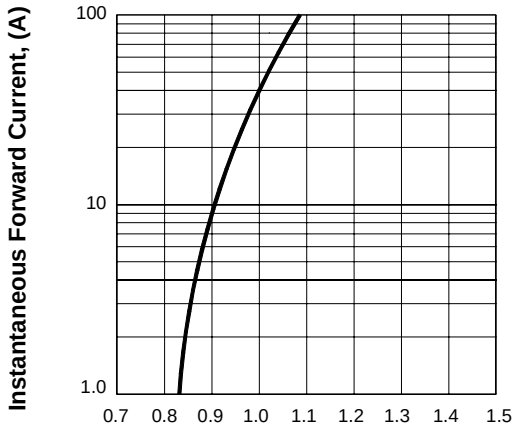

FIG.2 FORWARD DERATING CURVE

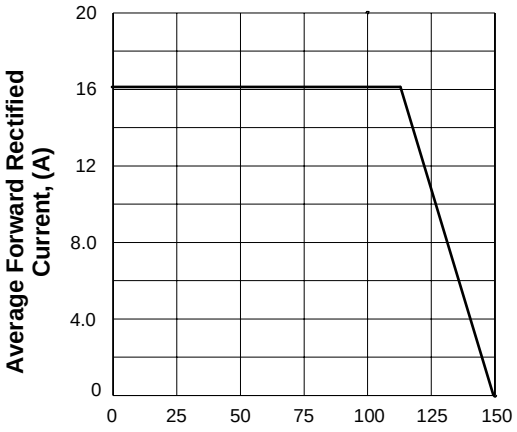

FIG.3 TYPICAL REVERSE CHARACTERISTICS

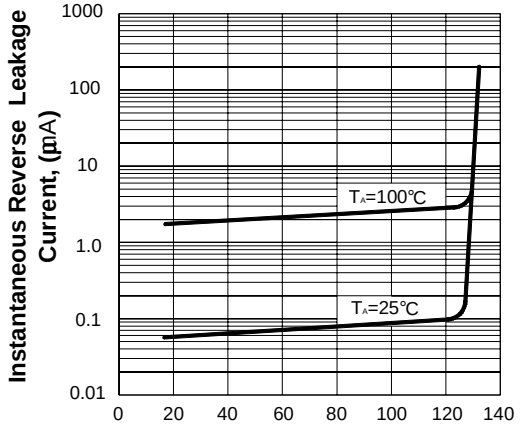

FIG.4 PEAK FORWARD SURGE CURRENT